

Radiation	Technology	Electrodes
Green	InGaN/Al ₂ O ₃	Both on top side

	typ. dimensions (μm)
	<p>typ. thickness 100 (±10) μm</p> <p>p and n contact gold alloy</p> <p>backside metalization gold alloy</p>

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		2.8	3.2	V
Forward voltage ¹⁾	I _F = 350 mA	V _F		3.6		V
Reverse voltage	I _R = 10 μA	V _R	5			V
Radiant power ¹⁾	I _F = 350 mA	Φ _e	80	110		mW
Luminous intensity ¹⁾	I _F = 20 mA	I _v	750	850		mcd
Luminous intensity ¹⁾	I _F = 350 mA	I _v	7500	9000		mcd
Peak wavelength	I _F = 350 mA	λ _p	505	515	525	nm
Dominant wavelength	I _F = 350 mA	λ _D	515	525	535	nm
Spectral bandwidth at 50%	I _F = 20 mA	Δλ _{0.5}		35		nm
Switching time	I _F = 20 mA	t _r , t _f		50		ns

¹⁾Measured on bare chip with *EPIGAP* equipment

Labeling

Type	Lot N°	I _v (typ) [mcd]	V _F (typ) [V]	Quantity
ELC-525-31-2				

Packing: Chips on adhesive film with wire-bond side on top

We reserve the right to make changes to improve technical design and may do so without further notice.
Parameters can vary in different applications. All operating parameters must be validated for each application by the customers themselves.